

MG17150D-BN4MM



Agency Approvals

| AGENCY | AGENCY FILE NUMBER |
|---|--------------------|
|  | E71639 |

Features

- IGBT³ CHIP(1700V Trench+Field Stop technology)
- Low turn-off losses, short tail current
- $V_{CE(sat)}$ with positive temperature coefficient
- DIODE CHIP(1700V EMCON 3 technology)
- Free wheeling diodes with fast and soft reverse recovery

Applications

- High frequency switching application
- Medical applications
- Motion/servo control
- UPS systems

Module Characteristics ($T_c = 25^\circ\text{C}$, unless otherwise specified)

| Symbol | Parameters | Test Conditions | Min | Typ | Max | Unit |
|--------------|----------------------------|------------------|-----|------|-----|------------------|
| $T_{J(max)}$ | Max. Junction Temperature | | | | 150 | $^\circ\text{C}$ |
| $T_{J(op)}$ | Operating Temperature | | -40 | | 125 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature | | -40 | | 125 | $^\circ\text{C}$ |
| V_{isol} | Insulation Test Voltage | AC, t=1min | | 4000 | | V |
| CTI | Comparative Tracking Index | | 350 | | | |
| Torque | Module-to-Sink | Recommended (M6) | 3 | | 5 | N·m |
| Torque | Module Electrodes | Recommended (M6) | 2.5 | | 5 | N·m |
| Weight | | | | 320 | | g |

Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$, unless otherwise specified)

| Symbol | Parameters | Test Conditions | Values | Unit |
|--------------|-----------------------------------|---|----------|----------------------|
| IGBT | | | | |
| V_{CES} | Collector - Emitter Voltage | $T_J=25^\circ\text{C}$ | 1700 | V |
| V_{GES} | Gate - Emitter Voltage | | ± 20 | V |
| I_C | DC Collector Current | $T_c=25^\circ\text{C}$ | 250 | A |
| | | $T_c=80^\circ\text{C}$ | 150 | A |
| I_{CM} | Repetitive Peak Collector Current | $t_p=1\text{ms}$ | 300 | A |
| P_{tot} | Power Dissipation Per IGBT | | 890 | W |
| Diode | | | | |
| V_{RRM} | Repetitive Reverse Voltage | $T_J=25^\circ\text{C}$ | 1700 | V |
| $I_{F(AV)}$ | Average Forward Current | $T_c=25^\circ\text{C}$ | 250 | A |
| | | $T_c=80^\circ\text{C}$ | 150 | A |
| I_{FRM} | Repetitive Peak Forward Current | $t_p=1\text{ms}$ | 300 | A |
| I^2t | | $T_J = 125^\circ\text{C}, t = 10\text{ms}, V_R = 0\text{V}$ | 4200 | A^2S |

Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

Electrical and Thermal Specifications ($T_c = 25^\circ\text{C}$, unless otherwise specified)

| Symbol | Parameters | Test Conditions | Min | Typ | Max | Unit |
|---------------|---|---|-------------------------|------|------|---------------|
| IGBT | | | | | | |
| $V_{GE(th)}$ | Gate - Emitter Threshold Voltage | $V_{CE}=V_{GE}, I_C=6.0\text{mA}$ | 5.2 | 5.8 | 6.4 | V |
| $V_{CE(sat)}$ | Collector - Emitter Saturation Voltage | $I_C=150\text{A}, V_{GE}=15\text{V}, T_J=25^\circ\text{C}$ | | 2.0 | 2.45 | V |
| | | $I_C=150\text{A}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}$ | | 2.4 | | V |
| I_{CES} | Collector Leakage Current | $V_{CE}=1700\text{V}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$ | | | 3 | mA |
| | | $V_{CE}=1700\text{V}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$ | | | 20 | mA |
| I_{GES} | Gate Leakage Current | $V_{CE}=0\text{V}, V_{GE}=\pm 20\text{V}, T_J=125^\circ\text{C}$ | -400 | | 400 | nA |
| R_{Gint} | Intergrated Gate Resistor | | | 4.3 | | Ω |
| Q_{ge} | Gate Charge | $V_{CE}=900\text{V}, I_C=150\text{A}, V_{GE}=\pm 15\text{V}$ | | 1.8 | | μC |
| C_{ies} | Input Capacitance | $V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$ | | 13.6 | | nF |
| C_{res} | Reverse Transfer Capacitance | | | 0.45 | | nF |
| $t_{d(on)}$ | Turn - on Delay Time | $V_{CC}=900\text{V}$ $I_C=150\text{A}$ $R_G=3.3\Omega$ $V_{GE}=\pm 15\text{V}$ Inductive Load | $T_J=25^\circ\text{C}$ | 380 | | ns |
| | | | $T_J=125^\circ\text{C}$ | 420 | | ns |
| t_r | Rise Time | | $T_J=25^\circ\text{C}$ | 50 | | ns |
| | | | $T_J=125^\circ\text{C}$ | 60 | | ns |
| $t_{d(off)}$ | Turn - off Delay Time | | $T_J=25^\circ\text{C}$ | 700 | | ns |
| | | | $T_J=125^\circ\text{C}$ | 900 | | ns |
| t_f | Fall Time | | $T_J=25^\circ\text{C}$ | 180 | | ns |
| | | | $T_J=125^\circ\text{C}$ | 300 | | ns |
| E_{on} | Turn - on Energy | | $T_J=25^\circ\text{C}$ | 33 | | mJ |
| | | | $T_J=125^\circ\text{C}$ | 48 | | mJ |
| E_{off} | Turn - off Energy | | $T_J=25^\circ\text{C}$ | 32 | | mJ |
| | | | $T_J=125^\circ\text{C}$ | 47 | | mJ |
| I_{SC} | Short Circuit Current | $t_{psc}\leq 10\mu\text{S}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}, V_{CC}=1000\text{V}$ | | 600 | | A |
| R_{thJC} | Junction-to-Case Thermal Resistance (Per IGBT) | | | | 0.14 | K/W |
| Diode | | | | | | |
| V_F | Forward Voltage | $I_F=150\text{A}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$ | | 1.8 | 2.2 | V |
| | | $I_F=150\text{A}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$ | | 1.9 | | V |
| I_{RRM} | Max. Reverse Recovery Current | $I_F=150\text{A}, V_R=900\text{V}$ | | 240 | | A |
| Q_{rr} | Reverse Recovery Charge | $di_f/dt=-3600\text{A}/\mu\text{s}$ | | 72 | | μC |
| E_{rec} | Reverse Recovery Energy | $T_J=125^\circ\text{C}$ | | 41 | | mJ |
| R_{thJCD} | Junction-to-Case Thermal Resistance (Per Diode) | | | | 0.21 | K/W |

Figure 1: Typical Output Characteristics

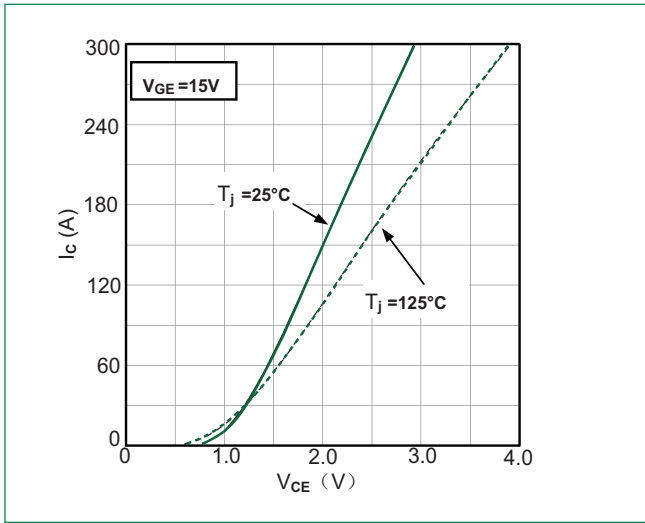


Figure 2: Typical Output Characteristics

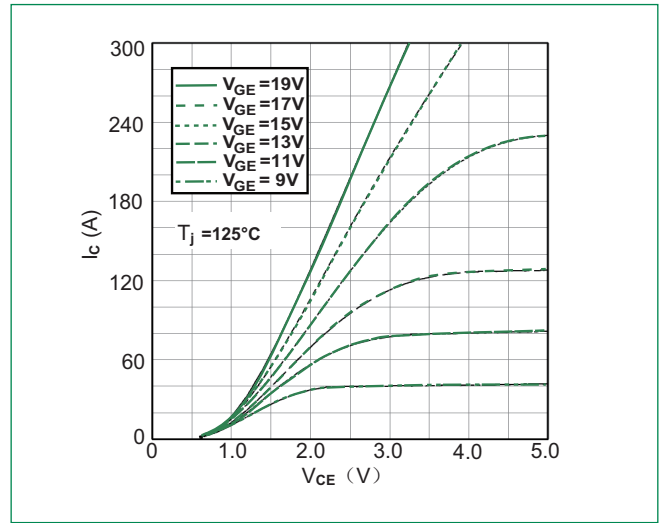


Figure 3: Typical Transfer characteristics

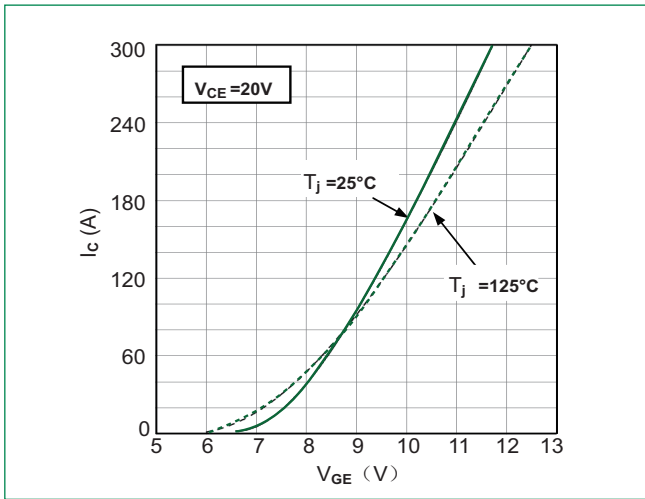


Figure 4: Switching Energy vs. Gate Resistor

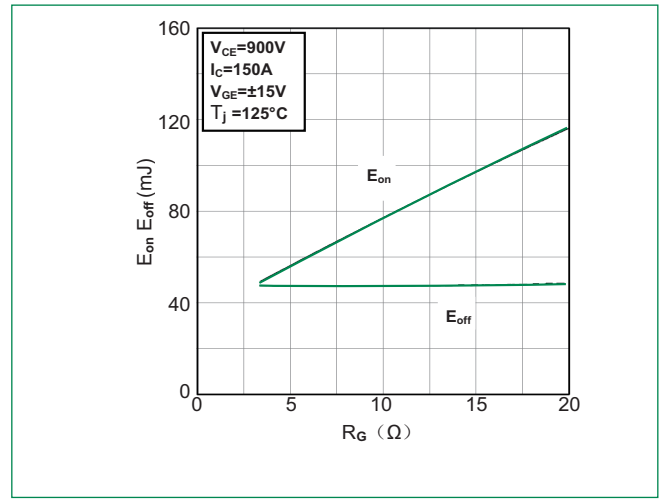


Figure 5: Switching Energy vs. Collector Current

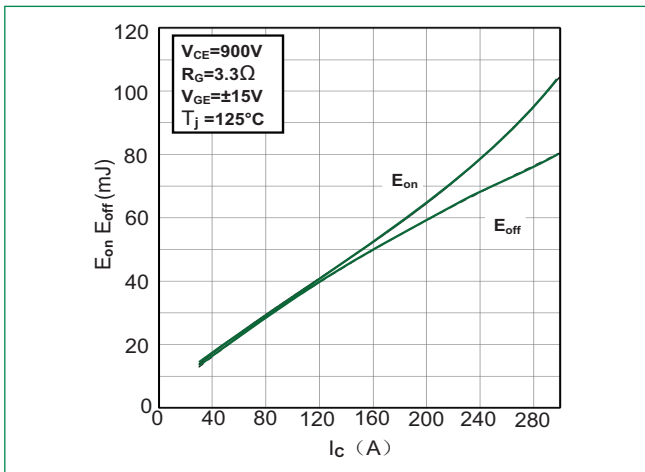


Figure 6: Reverse Biased Safe Operating Area

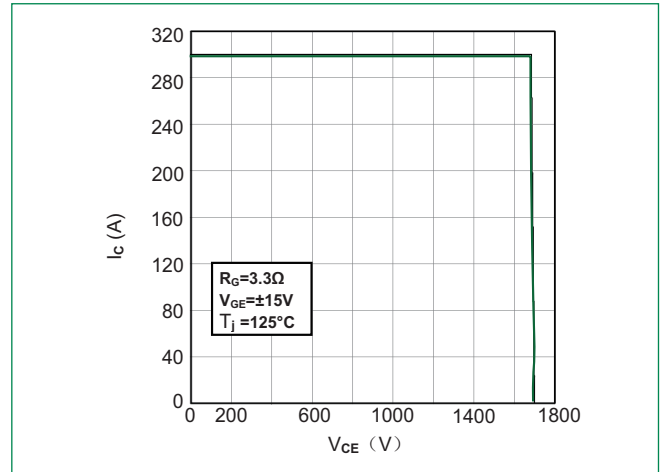


Figure 7: Diode Forward Characteristics

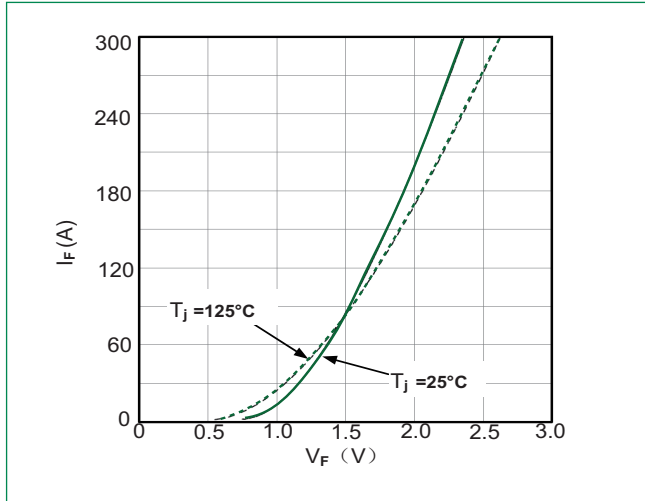


Figure 8: Switching Energy vs. Gate Resistor

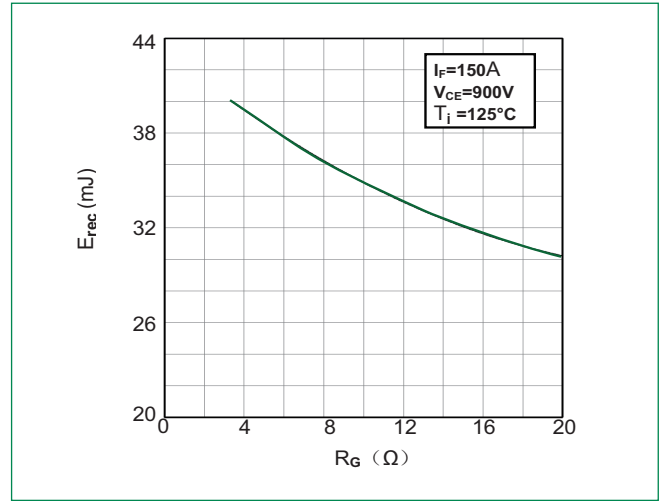


Figure 9: Switching Energy vs. Forward Current

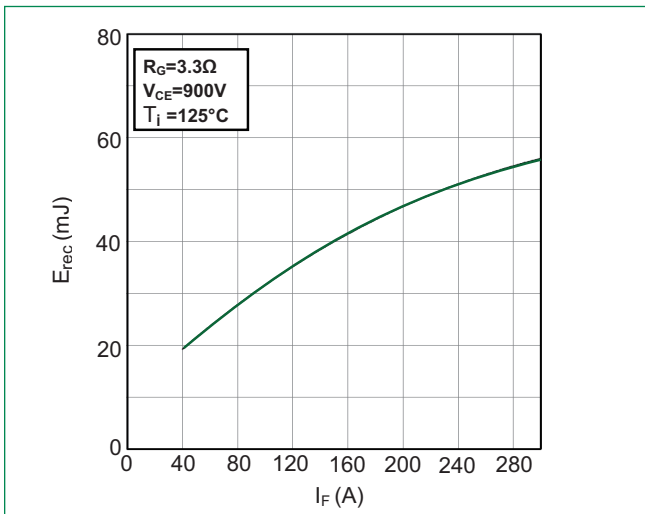
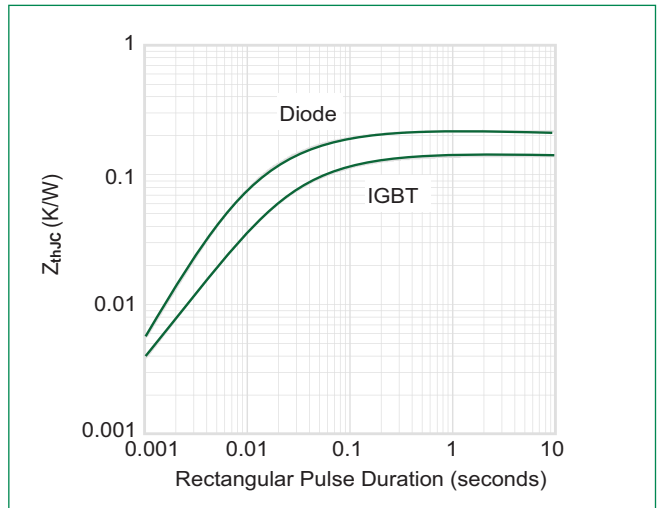
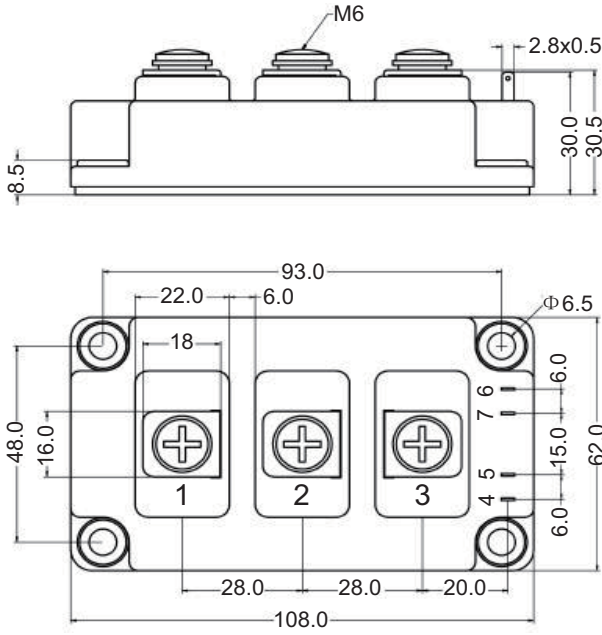


Figure 10: Transient Thermal Impedance of Diode and IGBT

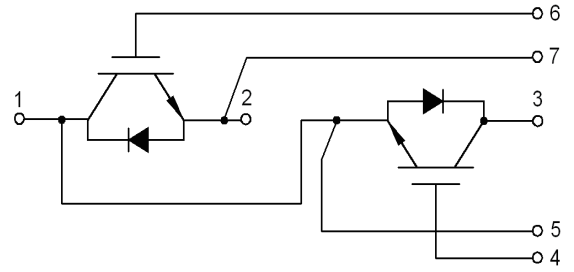


Dimensions-Package D



Dimensions in mm

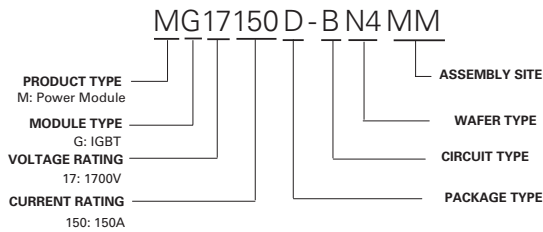
Circuit Diagram



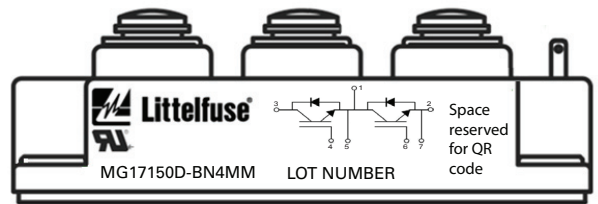
Packing Options

| Part Number | Marking | Weight | Packing Mode | M.O.Q |
|----------------|----------------|--------|--------------|-------|
| MG17150D-BN4MM | MG17150D-BN4MM | 320g | Bulk Pack | 30 |

Part Numbering System



Part Marking System



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На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9